#### Lecture 9

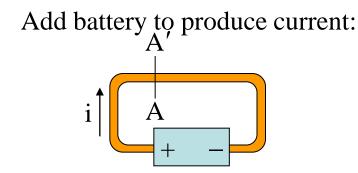
- In this lecture we will look at:
  - Charges and currents.
  - Current density.
  - The drift speed of charge carriers.
  - Resistance and resistivity.
  - Ohm's Law.
  - Conduction in metals.
  - Power in electric circuits.
  - Semiconductors and superconductors.

- After this lecture, you should be able to answer the following questions:
- The drift speed of the electrons carrying an electric current in a copper wire is typically only about 10<sup>-3</sup> ms<sup>-1</sup>. Why then does a light come on almost instantaneously when the switch is depressed even though it is 5 m away from the bulb?
- What is the difference between resistance and resistivity?
- Give three formulae for the power dissipated in a resistor R across which there is a potential V and through which a current i is flowing.

#### Charges and Currents

- Move from consideration of electrostatics to study of electric currents and their effects.
- Consider first steady ("direct") currents.
- For current to flow must be a net flow of charge.
- Electrons in an isolated loop of copper wire travel at about 10<sup>6</sup> ms<sup>-1</sup>, but no net flow of electrons, so no current.





- Charges move because electric field,
  E, established in copper and charges (electrons) feel force, F = Eq.
- Current through plane (e.g. A A'):  $i = \frac{dq}{dt}$  [9.1]
- If i constant, i = q/t [9.2]
- Charge from current through:

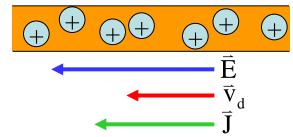
$$q = \int dq = \int_{0}^{t} i dt' \qquad [9.3]$$

If i constant, q = it [9.4]

# Current Density and Drift Speed of Charge Carriers

- Unit of current is ampere ( $A = C s^{-1}$ ).
- Current direction taken to be direction in which +ive charge travels.
- Arrows often used to indicate current direction, but current is scalar, not vector quantity.
- Current density J is vector quantity with direction given by that of the velocity of the moving +ive charges (or opposite to direction of velocity of –ive charges).
- Magnitude of  $\overline{J}$  is current per unit area.
- Units of current density, A m<sup>-2</sup>.

- Hence calculate current from current density:  $i = \int \vec{J} \cdot d\vec{A}$  [9.5]
- If current is uniform and perpendicular to area A, J = i/A [9.6]
- In metals, current is due to drift of electrons.



- If there are n charge carriers per unit volume, sum of charge of carriers in length L is q = nALe.
- This moves through plane in wire in time  $t = L/v_d$ .
- Hence  $i = q/t = nAv_de$ .

## Drift Speed, Resistance and Resistivity

- Solve for  $v_d$  to get:  $v_d = \frac{i}{nAe} = \frac{J}{ne}$  [9.7]
- In vector form:  $\vec{J} = ne \vec{v}_d$ .
- Note,  $v_d$  typically  $10^{-3}$  m s<sup>-1</sup>!
- Current through conductor related to potential difference across it through resistance, defined by:

$$R = \frac{V}{i} \qquad [9.8]$$

- Unit ohm ( $\Omega = V A^{-1}$ ).
- i = V/R, so increasing R reduces current: "resistance" aptly named!
- Resistance is property of an object (a particular component in a circuit).

Resistivity,  $\rho$ , is property of material.

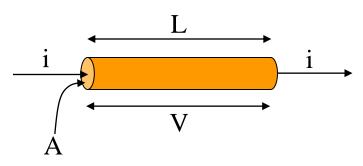
• Defined by: 
$$\rho = \frac{E}{J}$$
 [9.9]

• Units 
$$\frac{V/m}{A/m^2} = \frac{V}{A}m = \Omega m.$$

- In vector form,  $\vec{E} = \rho \vec{J}$ .
- Eqn.s for  $\rho$  only for isotropic materials.
- Conductivity σ is reciprocal of resistivity, conductance G reciprocal of resistance.
- Units of  $\sigma$  are S m<sup>-1</sup>, of G are S (S = Siemens or mho =  $\Omega^{-1}$ ).
- From above,  $\vec{J} = \sigma \vec{E}$  and  $G = \frac{i}{V}$

# Calculating Resistance from Resistivity

Calculate the resistance of a length L of wire of cross-sectional area A and resistivity ρ.



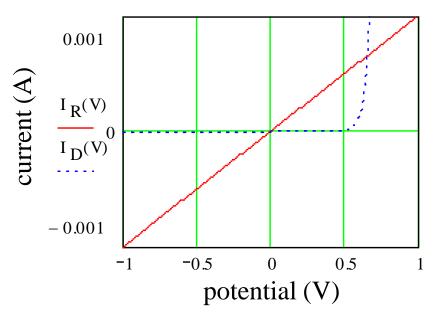
- Assume E field and current density uniform throughout wire.
- Hence E = V/L and J = i/A.

• 
$$\rho = \frac{E}{J} = \frac{V/L}{i/A} = R \frac{A}{L}$$
.  
• So we have  $R = \frac{\rho L}{A}$  [9.10]

- Resistivity varies with temperature, T.
- For metals, the variation is fairly linear over a broad range of T.
- Choose a reference temp.  $T_0$  at which the resistivity is  $\rho_0$ .
- (Usually  $T_0 = 293$  K, ~ room temp.)
- Can then write:  $\rho - \rho_0 = \alpha \rho_0 (T - T_0)$  [9.11]
- The quantity α is the temperature coefficient of resistance.
- For copper:
  - $\rho_0 = 1.69 \times 10^{-8} \,\Omega \,m.$
  - $\alpha = 4.3 \times 10^{-3} \text{ K}^{-1}$ .

#### Ohm's Law

Contrast the behaviour of the current through two devices illustrated below:



For device "R", the current is proportional to the voltage.

- For device "D", the current is small until V > 0.6 V at which point it increases sharply.
- "R" obeys Ohm's law, "D" does not.
- Ohm's law states: The current through a device is directly proportional to the potential difference applied to the device.
- This holds for a resistance, as i = V/R with R the same for all V.
- (Note that V = iR holds even for devices that do not obey Ohm's law, where R is the resistance at that potential: devices obey Ohm's law when the same value of R holds for all potential differences!)

# Conduction in Metals and Ohm's Law

- Charge transport in metals occurs as (some) electrons are free to move.
- These have speeds of about 10<sup>6</sup> ms<sup>-1</sup> and "bounce around" inside the metal, colliding with atoms on average every τ seconds.
- If an electric field is applied, the electrons experience a force F = eE and hence an acceleration

 $a = \frac{F}{m_e} = \frac{eE}{m_e}.$ 

 Between collisions they acquire a drift speed due to the E field of

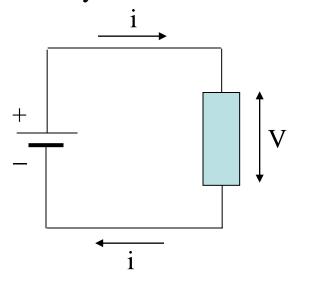
$$v_{d} = \frac{eE}{m_{e}}\tau.$$

Hence 
$$\vec{J} = ne\vec{v}_d = ne\frac{e\vec{E}}{m_e}\tau = \frac{ne^2\vec{E}}{m_e}\tau$$
.  
But  $\vec{J} = \frac{\vec{E}}{\rho}$  so  $\rho = \frac{m_e}{ne^2\tau}$ .

- As  $v_d \ll 10^6 \text{ ms}^{-1}$ ,  $\tau$  is approximately independent of E and therefore so is  $\rho$ .
- Hence metals obey Ohm's law.

# Power in Electric Circuits

Consider a device connected to a battery:



- A charge dq passes through the device in a time dt with dq = i dt.
- In passing through the device, the charge moves through a potential difference of V.

- Hence, the potential energy decreases by dU = V dq = i dt V.
- The power dissipated in the device (rate of energy transfer) is thus  $P = \frac{dU}{dt} = iV \qquad [9.12]$
- Unit of power is the Watt (W = V A).
- Combining with the expressions
  V = i R and i = V / R we get:

$$P = i^2 R$$
 [9.13]

and P = 
$$\frac{V^2}{R}$$
 [9.14]

# Superconductors and Semiconductors

- Superconductivity is observed in some materials, e.g. mercury.
- For these materials, below a certain critical temperature (about 4 K for mercury), the resistance drops to zero.
- Semiconductors, like silicon, have a resistivity that is between that of metals and insulators.
- In metals, some of the "outer" electrons are only loosely bound and can be caused to move through the metal by the application of an E field.
- In insulators all the electrons are tightly bound.

- In semiconductors, some electrons can be freed by thermal energy.
- Hence the resistivity of a semiconductor is a strong function of its temperature.

Property	Copper	Silicon
Type of material	Metal	Semiconductor
Charge carrier density n (m <sup>-3</sup> )	9 x 10 <sup>28</sup>	9 x 10 <sup>16</sup>
Resistivity ρ (Ωm)	2 x 10 <sup>-8</sup>	3 x 10 <sup>3</sup>
Temp. Coeff. of resistance $\alpha$ (K <sup>-1</sup> )	+2 x 10 <sup>-3</sup>	−70 x 10 <sup>-3</sup>